

Model No.: FYS-8011A/BX-XX

■ Absolute maximum ratings

(Ta=25°C)

Parameter	Symbol	Test Condition	Value		Unit
			Min	Max	
Reverse Voltage	VR	IR=30	5	—	V
Forward Current	IF	—	—	30	mA
Power Dissipation	Pd	—	—	100	mW
Pulse Current	Ipeak	Duty=0.1mS,1KHz	—	150	mA
Operating Temperature	Topr	—	-40	+85	°C
Storage Temperature	Tstr	—	-40	+85	°C

■ Electrical-Optical Characteristics

● Color Code & Chip Characteristics:(Test Condition:IF=20mA)

(Ta=25°C)

Emitting Color	Dice Material	Peak Wave Length(λ_p)	Spectral Line halfwidth($\Delta\lambda/2$)	Forward Voltage(VF) Unit:V		Luminous Intensity (Iv) Unit:mcd	
				Typ	Max		
Standard brightness							
H	Red	GaP	700nm	90nm	2.00	2.50	1
S	Hi Red	AlGaAs/SH	660nm	20nm	1.80	2.50	15~20
D	Super Red	AlGaAs/DH	650nm	20nm	1.90	2.50	26~38
E	Orange	GaAsP	625nm	35nm	1.90	2.50	14~20
A	Amber	GaAsP	610nm	35nm	1.90	2.50	13~18
Y	Yellow	GaAsP	590nm	35nm	1.90	2.50	13~18
G	Green	GaP	570nm	10nm	1.90	2.50	14~18
B	Blue	InGaN	430nm	60nm	3.40	4.40	0.7~1(mw)
			460nm		2.80	3.80	6~12(mw)
			470nm		2.80	3.80	6~12(mw)
PG	Pure Green	InGaN	520nm	36nm	2.80	3.80	4~6(mw)
W	White	InGaN	X=0.29,Y=0.30	CCT:9500K	2.80	3.80	20~30
Ultra brightness							
UHR	Ultra Hi Red	AlGaInP	640nm	20nm	1.90	2.50	30~60
UR	Ultra Red	AlGaInP	635nm	20nm	1.90	2.50	60~100
UE	Ultra Orange	AlGaInP	625nm	20nm	1.90	2.50	60~120
UA	Ultra Amber	AlGaInP	610nm	20nm	1.90	2.50	40~100~150
UY	Ultra Yellow	AlGaInP	590nm	20nm	1.90	2.50	50~140~190
UG	Ultra Green	AlGaInP	570nm	30nm	1.90	2.50	30~60~80
PG	Ultra Pure Green	InGaN	520nm	36nm	2.80	3.80	260~310
BG	Ultra Bluish Green	InGaN	505nm	36nm	2.80	3.80	260~310
UB	Ultra Blue	InGaN	460nm	30nm	2.80	3.80	80~90~120
			470nm	30nm	2.80	3.80	80~90~120
UW	Ultra White	InGaN	X=0.29,Y=0.30	CCT:9500K	2.80	3.80	180~200
Segment-to-Segment Luminous Intensity ratio(Iv-M)				1.5:1			